

N-Channel 12 V (D-S) MOSFET

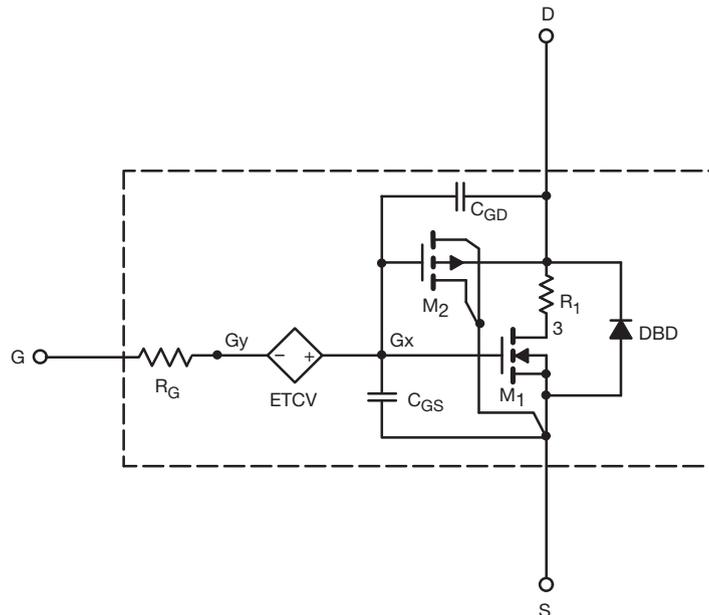
DESCRIPTION

The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the - 55 °C to + 125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage. A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the - 55 °C to + 125 °C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



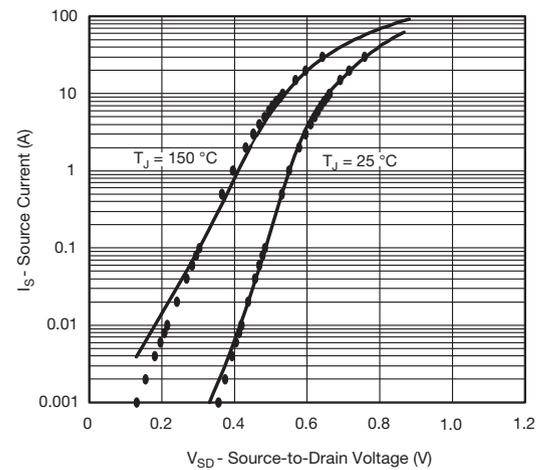
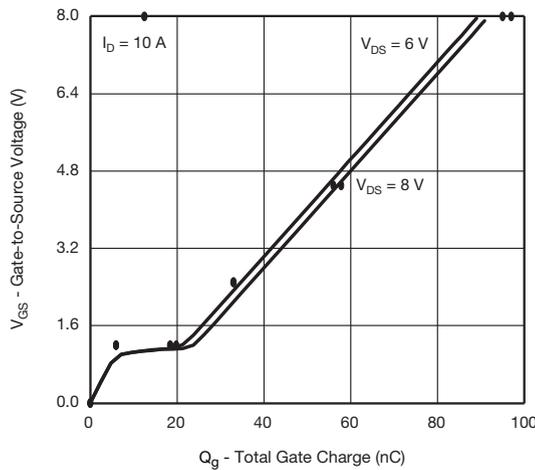
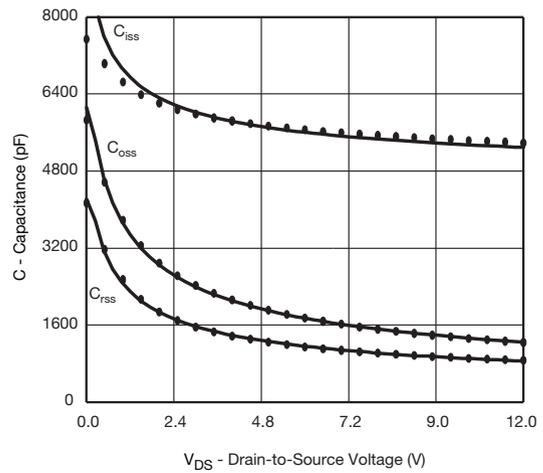
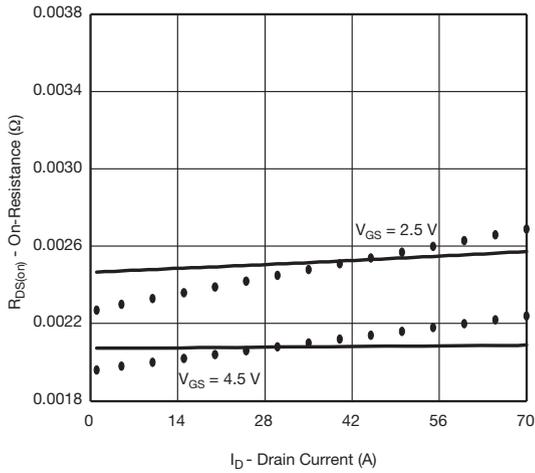
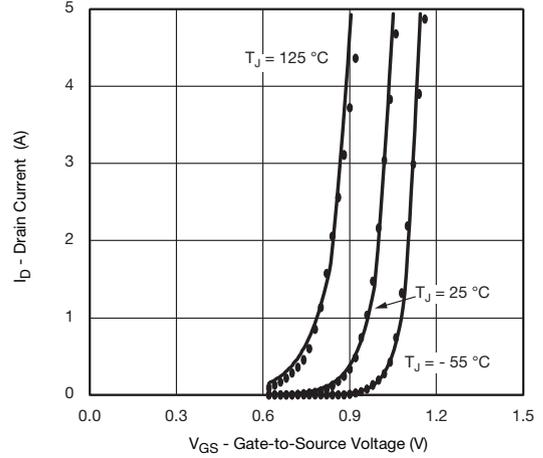
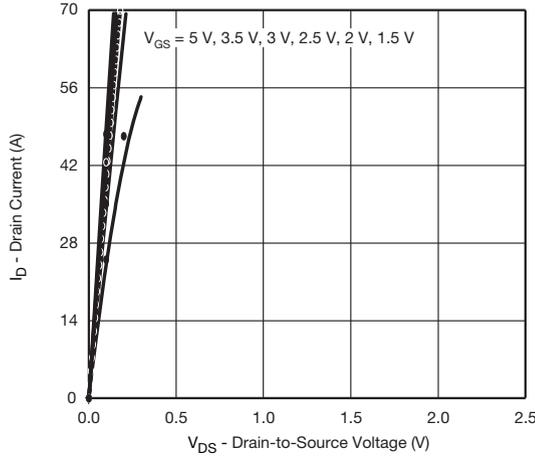
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.45	-	V
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 15 A	0.0021	0.0020	Ω
		V _{GS} = 2.5 V, I _D = 12 A	0.0024	0.0023	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 15 A	102	105	S
Body Diode Voltage	V _{SD}	I _S = 5 A	0.61	0.62	V
Dynamic^b					
Input Capacitance	C _{iss}	V _{DS} = 6 V, V _{GS} = 0 V, f = 1 MHz	5610	5760	pF
Output Capacitance	C _{oss}		1750	1730	
Reverse Transfer Capacitance	C _{rss}		1160	1145	
Total Gate Charge	Q _g	V _{DS} = 6 V, V _{GS} = 4.5 V, I _D = 10 A	55	56	nC
Gate-Source Charge	Q _{gs}	V _{DS} = 6 V, V _{GS} = 2.5 V, I _D = 10 A	35	33	
Gate-Source Charge	Q _{gs}		5.9	5.9	
Gate-Drain Charge	Q _{gd}		12.5	12.5	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.